

ABSTRACT

A sputtering target according to the present invention has a molybdenum content of from 3 to 25 mol%, and a silicon content of from 75 to 97 mol%. The sputtering target includes a silicon phase in which an average grain size of silicon grains is 2.0 μm or less, and a molybdenum silicide phase in which an average grain size of molybdenum silicide grains is 2.5 μm or less. The average number of holes present in the silicon phase and having a major axis of 0.3 μm or greater is ten or fewer within an area of 90 $\times$ 125 μm .